# **74AUP2G07**

# Low-power dual buffer with open-drain output Rev. 7 — 29 November 2012

**Product data sheet** 

#### **General description** 1.

The 74AUP2G07 provides two non-inverting buffers with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V<sub>CC</sub> range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

#### 2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static-power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



### Low-power dual buffer with open-drain output

## 3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AUP2G07GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363					
74AUP2G07GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886					
74AUP2G07GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891					
74AUP2G07GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115					
74AUP2G07GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 $\times$ 1.0 $\times$ 0.35 mm	SOT1202					

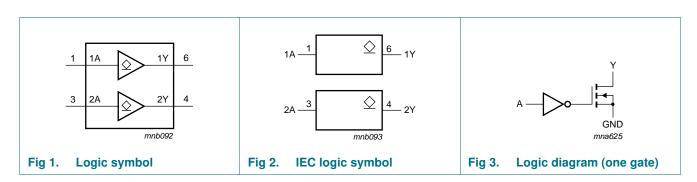
## 4. Marking

#### Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP2G07GW	p7
74AUP2G07GM	p7
74AUP2G07GF	p7
74AUP2G07GN	p7
74AUP2G07GS	p7

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

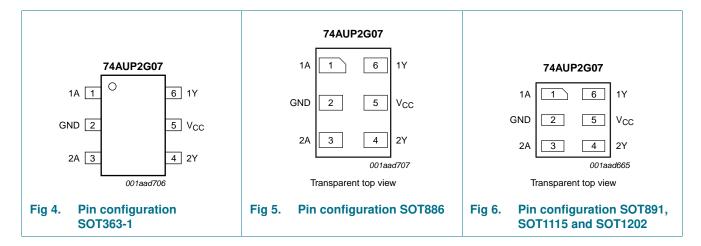
## 5. Functional diagram



Low-power dual buffer with open-drain output

## 6. Pinning information

#### 6.1 Pinning



## 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V <sub>CC</sub>	5	supply voltage
1Y	6	data output

## 7. Functional description

Table 4. Function table[1]

Input	Output
nA	nY
L	L
H	Z

- [1] H = HIGH voltage level;
  - L = LOW voltage level;
  - Z = high-impedance OFF state.

#### Low-power dual buffer with open-drain output

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		[ <u>1</u> ] -0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	20	mA
I <sub>CC</sub>	supply current		-	50	mA
$I_{GND}$	ground current		-50	-	mA
$T_{\text{stg}}$	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] -	250	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## 9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		8.0	3.6	V
$V_{I}$	input voltage		0	3.6	V
V <sub>O</sub>	output voltage	Active mode and Power-down mode	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V <sub>CC</sub> = 0.8 V to 3.6 V	0	200	ns/V

### 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbo	I Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> =	25 °C					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V

74AUP2G07

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<sup>[2]</sup> For SC-88 package: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## Low-power dual buffer with open-drain output

**Table 7. Static characteristics** ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	٧
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{\text{CC}}$	٧
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	٧
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	٧
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	٧
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	٧
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	٧
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	٧
l <sub>l</sub>	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μА
l <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μА
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μА
Δl <sub>CC</sub>	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$	-	0.7	-	рF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	0.9	-	рF
T <sub>amb</sub> = -	40 °C to +85 °C					
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.70 \times V_{CC}$	-	-	٧
V <sub>IH</sub>	, -	V <sub>CC</sub> = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	٧
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	٧
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	٧
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	$0.30 \times V_{CC}$	٧
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	٧
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	٧
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	٧
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	٧
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	٧
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	٧
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	٧
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	٧
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	٧
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	٧
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	٧
l <sub>l</sub>	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ ; $V_O = 0 \text{ V to } 3.6 \text{ V}$ ; $V_{CC} = 0 \text{ V}$ to 3.6 V	-	-	±0.5	μΑ

## Low-power dual buffer with open-drain output

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
I <sub>CC</sub>	supply current	$V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.9	μΑ
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
T <sub>amb</sub> = -	40 °C to +125 °C					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	$0.25 \times V_{CC}$	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}$ ; $V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I <sub>I</sub>	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μА
I <sub>CC</sub>	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μА
$\Delta I_{CC}$	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

## Low-power dual buffer with open-drain output

## 11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		-4	0 °C to +	125 °C	Unit
				Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pl	F			'	'				
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7							
		$V_{CC} = 0.8 V$	-	11.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.1	4.1	7.5	1.7	9.1	10.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	1.6	3.0	5.1	1.3	6.1	6.7	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.6	2.7	4.0	1.2	5.0	5.5	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.1	2.1	3.2	0.9	4.0	4.4	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.4	2.2	2.8	1.1	3.3	3.6	ns
C <sub>L</sub> = 10	pF								
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7							
		$V_{CC} = 0.8 V$	-	14.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.0	5.1	9.0	2.4	11.2	12.3	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.3	3.8	6.1	2.0	7.4	8.1	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.4	3.6	4.8	1.8	6.1	6.7	ns
		$V_{CC}$ = 2.3 V to 2.7 V	1.7	2.8	3.8	1.3	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.2	3.1	4.2	1.6	4.5	5.0	ns
C <sub>L</sub> = 15	pF								
$t_{pd}$	propagation delay	nA to nY; see Figure 7							
		$V_{CC} = 0.8 V$	-	17.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.5	6.1	10.4	3.2	13.1	14.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.0	4.5	6.8	2.6	8.6	9.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.8	4.4	6.7	2.2	7.8	8.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.4	3.4	4.5	1.9	5.3	5.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.2	4.0	5.7	1.9	6.1	6.7	ns
C <sub>L</sub> = 30	pF								
$t_{pd}$	propagation delay	nA to nY; see Figure 7							
		$V_{CC} = 0.8 V$	-	26.7	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.8	9.0	15.6	4.3	18.8	20.7	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	4.1	6.7	9.4	3.7	11.8	13.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	3.8	6.8	9.7	3.2	11.0	12.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	3.7	5.2	6.7	3.0	7.1	7.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	3.6	6.4	9.7	2.8	10.4	11.4	ns

#### Low-power dual buffer with open-drain output

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		25 °C —40 °C to +125 °C			125 °C	Unit
			N	/lin	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pl	F, 10 pF, 15 pF and	30 pF								
$C_{PD}$	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3][4]							
	capacitance	$V_{CC} = 0.8 \text{ V}$		-	0.5	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	0.6	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	0.6	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	0.7	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	0.9	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	1.2	-	-	-	-	pF

- [1] All typical values are measured at nominal  $V_{CC}$ .
- [2]  $t_{pd}$  is the same as  $t_{PZL}$  and  $t_{PLZ}$ .
- [3] All specified values are the average typical values over all stated loads.
- [4]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N$  where:

f<sub>i</sub> = input frequency in MHz;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching.

#### 12. Waveforms

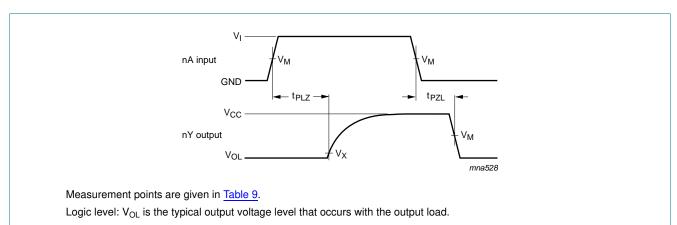
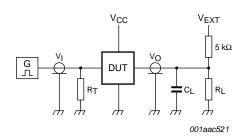


Fig 7. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output			
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>		
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.1 V		
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.15 V		
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.3 V		

#### Low-power dual buffer with open-drain output



Test data is given in Table 10.

Definitions for test circuit:

R<sub>L</sub> = Load resistance.

C<sub>L</sub> = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

 $V_{\text{EXT}}$  = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

#### Table 10. Test data

Supply voltage Input		Load		V <sub>EXT</sub>			
V <sub>CC</sub>	VI	t <sub>r</sub> , t <sub>f</sub>	C <sub>L</sub>	R <sub>L</sub> [1]	$t_{PLH}$ , $t_{PHL}$	$t_{PZH}$ , $t_{PHZ}$	$t_{PZL},t_{PLZ}$
0.8 V to 3.6 V	$V_{CC}$	$\leq$ 3 ns	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2\times V_{CC} \\$

<sup>[1]</sup> For measuring enable and disable times  $R_L$  = 5 k $\Omega$ , for measuring propagation delays, set-up and hold times and pulse width  $R_L$  = 1 M $\Omega$ .

#### Low-power dual buffer with open-drain output

## 13. Package outline

#### Plastic surface-mounted package; 6 leads

**SOT363** 

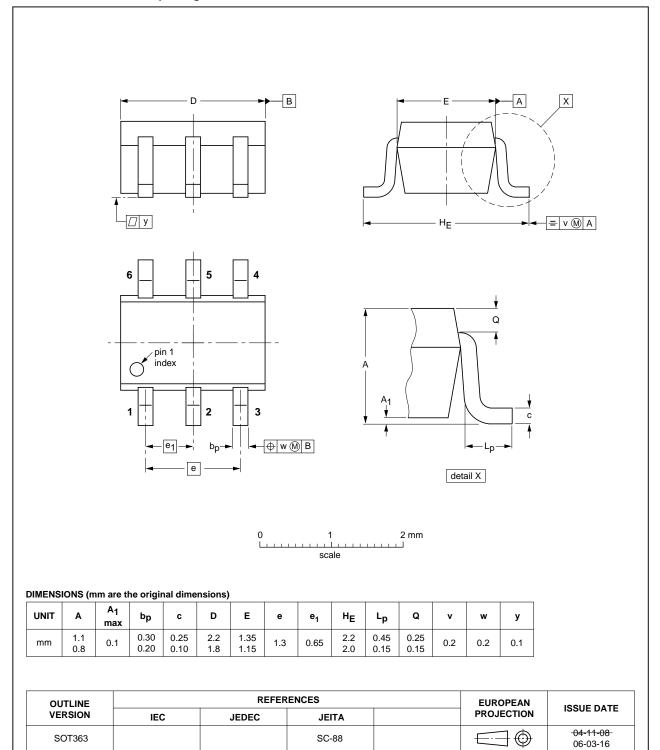


Fig 9. Package outline SOT363 (SC-88)

#### Low-power dual buffer with open-drain output

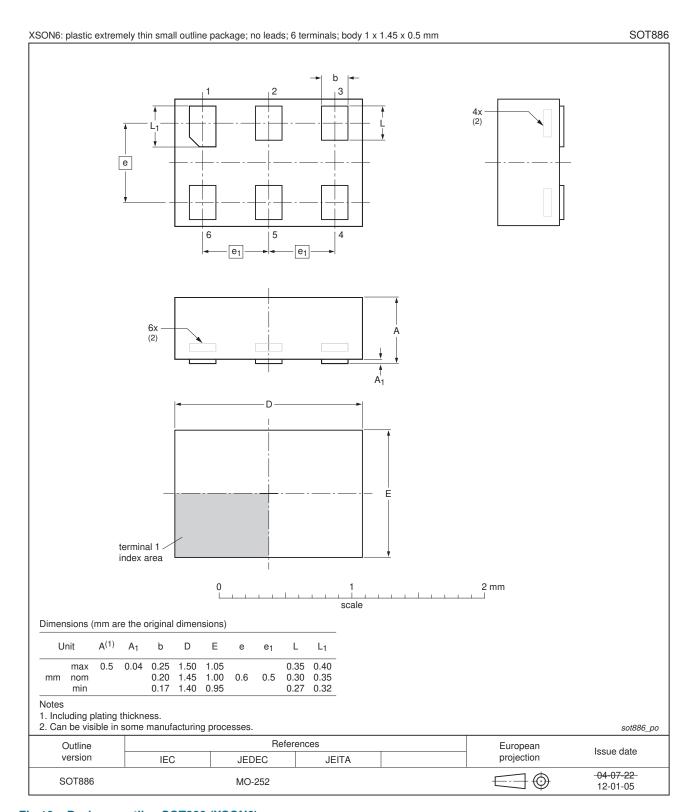


Fig 10. Package outline SOT886 (XSON6)

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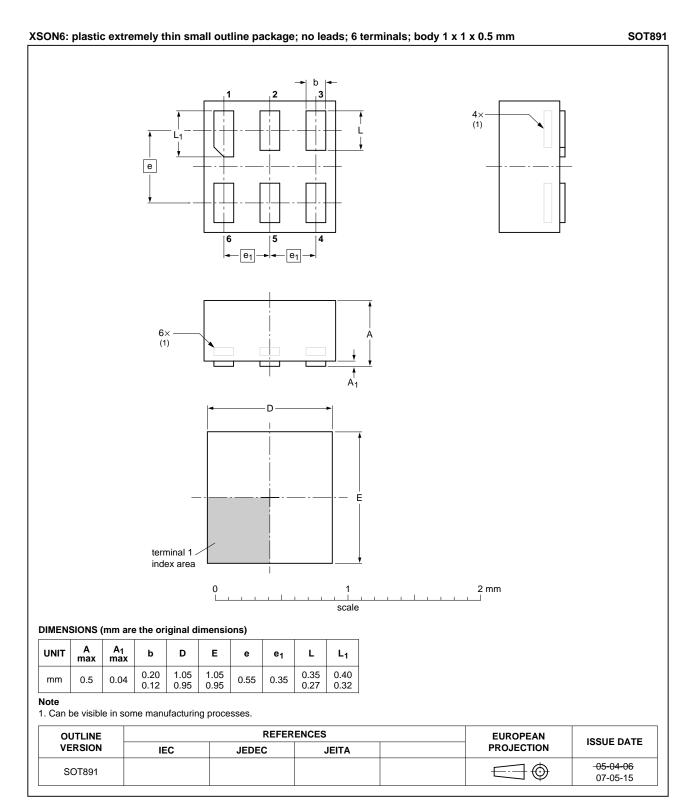


Fig 11. Package outline SOT891 (XSON6)

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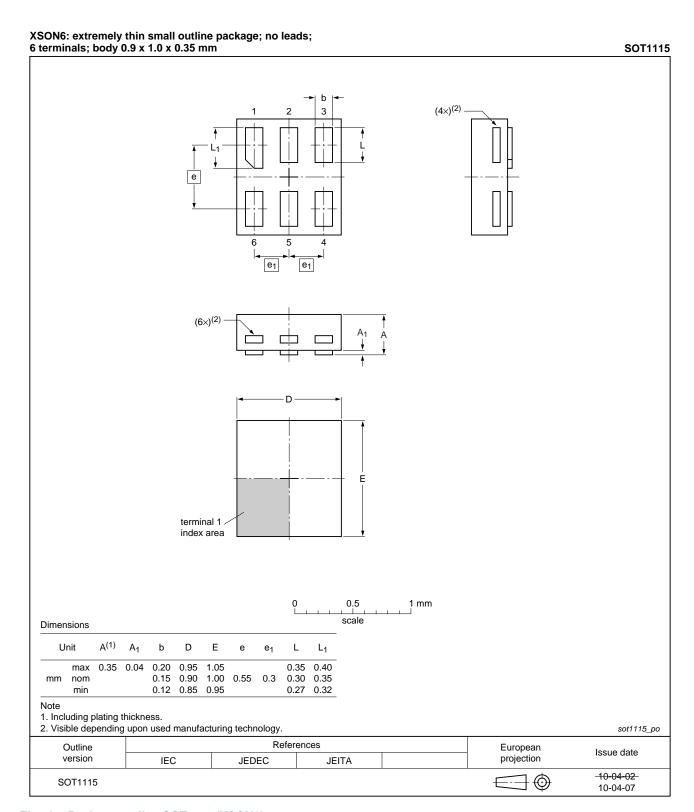


Fig 12. Package outline SOT1115 (XSON6)

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#### Low-power dual buffer with open-drain output

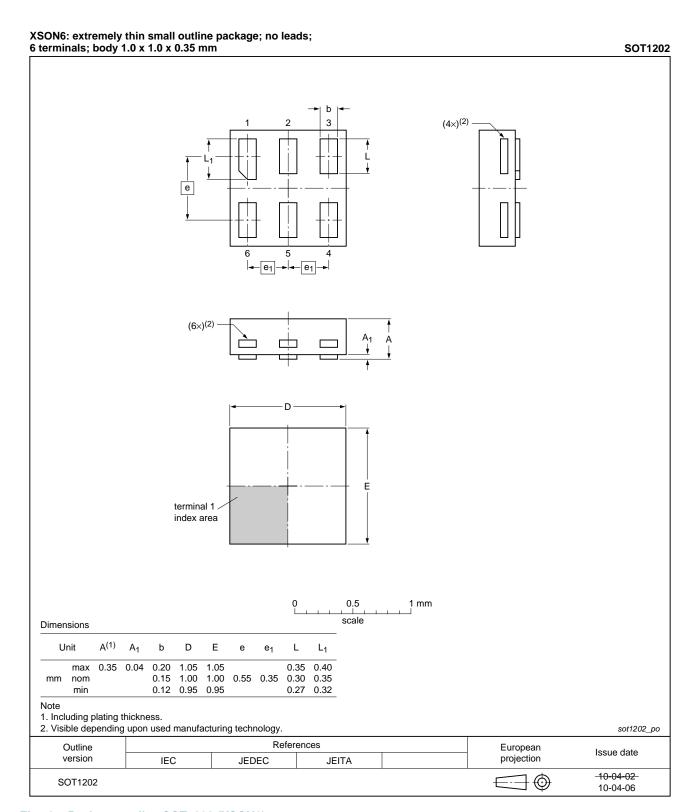


Fig 13. Package outline SOT1202 (XSON6)

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## Low-power dual buffer with open-drain output

## 14. Abbreviations

#### Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

## 15. Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G07 v.7	20121129	Product data sheet	-	74AUP2G07 v.6
Modifications:	<ul> <li>Package ou</li> </ul>	tline drawing of SOT886 (F	igure 10) modified.	
74AUP2G07 v.6	20111202	Product data sheet	-	74AUP2G07 v.5
74AUP2G07 v.5	20100909	Product data sheet	-	74AUP2G07 v.4
74AUP2G07 v.4	20090611	Product data sheet	-	74AUP2G07 v.3
74AUP2G07 v.3	20071016	Product data sheet	-	74AUP2G07 v.2
74AUP2G07 v.2	20070612	Product data sheet	-	74AUP2G07 v.1
74AUP2G07 v.1	20061121	Product data sheet	-	-

#### Low-power dual buffer with open-drain output

## 16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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